

Sheet 1 of 2

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 118072		APPLICATION NO. 10/733,455	
INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)				APPLICANT Masahiro KANAI			
				FILING DATE December 12, 2003			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
NTW	1	6,255,166 B1	07/03/2001	Ogura et al.			
	2	5,408,115	04/18/1995	Chang			
	3	5,696,383	10/19/1999	Chang et al.			
	4	5,422,504	06/06/1995	Chang et al.			
	5	5,494,838	02/27/1996	Chang et al.			
	6	6,177,318 B1	01/23/2001	Ogura et al.			
	7	6,248,633 B1	06/19/2001	Ogura et al.			
	8	6,587,381	07/01/2003	Kanai et al.			
	9	6,587,380	07/01/2003	Kanai et al.			
	10	6,646,916	11/11/2003	Kamei			
	11	2003-0072191	04/17/2003	Kamei			
	12	2003-0072194	04/17/2003	Kamei			
	13	6,707,720	03/16/2004	Kamei et al.			
	14	6,650,591	11/18/2003	Owa			
	15	2002-0191453	12/19/2002	Owa			
	16	6,707,695	03/16/2004	Owa			
	17	2003-0025150	02/06/2003	Kanai et al.			
	18	2003-0020123	01/30/2003	Kanai			
	19	2003-0048674	03/13/2003	Kanai			
	20	2003-0034530	02/20/2003	Kamei			
	21	2003-0031064	02/13/2003	Natori			
	22	2003-0027411	02/06/2003	Kamei			
	23	2003-0025149	02/06/2003	Kamei			
	24	2003-0123303	07/03/2003	Kamei			
	25	2003-0179609	09/25/2003	Natori			
	26	2003-0095443	05/22/2003	Natori			
	27	2003-0076717	04/24/2003	Natori			
NTW	28	2003-0103388	06/05/2003	Natori			

Date: April 9, 2004

NTN	29	2003-0137875	07/24/2003	Natori		
	30	2003-0146450	08/07/2003	Natori		
	31	2003-0151070	08/14/2003	Natori		
	32	2003-0179621	09/25/2003	Kamei et al.		
	33	2003-0164517	09/04/2003	Kamei et al.		
	34	2003-0174558	09/18/2003	Kamei et al.		
	35	2003-0198102	10/23/2003	Kamei et al.		
	36	6,707,742	03/16/2004	Kamei et al.		
	37	2003-0198103	10/23/2003	Kamei et al.		
	38	2003-0185054	10/02/2003	Kamei		
	39	2004-0013018	01/22/2004	Kanai		
	40	2004-0013027	01/22/2004	Kanai		
	41	2004-0061139	04/01/2004	Natori		
NTN	42	10/728,746	12/08/2003	Natori		

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
NTN	43	JP A 6-181319 (with abstract and translation)	06/28/1994	Japan		
	44	JP A 11-74389 (with abstract and translation)	03/16/1999	Japan		
	45	JP B1 2978477 (with abstract and translation)	09/10/1999	Japan		
	46	JP A 7-161851 (with abstract and translation)	06/23/1995	Japan		
NTN	47	JP A 2001-156188 (with abstract and translation)	06/08/2001	Japan		

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

NTN	48	Hayashi et al. "Twin MONOS Cell with Dual Control Gates", 2000 Symposium on VLSI Technology Digest of Technical Papers, 2000 IEEE
	49	Chang et al. "A New SONOS Memory Using Source-Side Injection for Programming", IEEE Electron Device Letters, Vol. 19, No. 7, July 1998, pp 253-255
NTN	50	Chen et al. "A Novel Flash Memory Device with Split Gate Source Side Injection and ONO Charge Storage Stack (SPIN), 1997 Symposium on VLSI Technology Digest of Technical Papers", pp 63-64

EXAMINER

Nam Nguyen

DATE CONSIDERED

11/5/04

Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.